

FTV05BCSOT883

ESD PROTECTION DIODE

Discription

The FTV05BCSOT883 isdesignedtoprotect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time ,make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

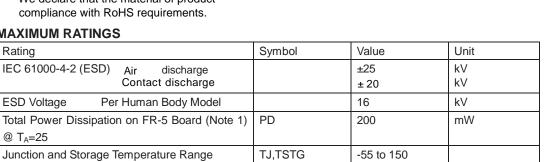
Applications

- Cellular phones audio
- MP3 players
- Digital cameras
- Portable applicationss
- mobile telephone

Features

- Small Body Outline Dimensions: 0.039" X 0.024"(1.0mmX0.6mm)
- Low Body Height: 0.020"(0.50mm)
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices
- We declare that the material of product compliance with RoHS requirements.

MAXIMUM RATINGS



260

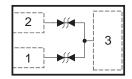
Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

TL

1. FR-5 = 1.0*0.75*0.62 in.

Second Duration)





Ordering information

Device	Marking	Shipping			
FTV05BCSOT883	P2	10000/Tape&Reel			

Lead Solder Temperature - Maximum (10

First Silicon

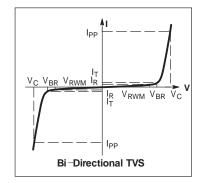


FTV05BCSOT883

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ IPP					
V _{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ VRWM					
V _{BR}	Breakdown Voltage @ IT					
Ι _Τ	Test Current					
P _{pk}	Peak Power Dissipation					
С	Capacitance @ VR = 0 and f = 1.0 MHz					



ELECTRICAL CHARACTERISTICS

	V _{RWM} (V)	I _{R1} (μΑ) @ V _{RWM}	I _{R2} (μΑ) @ V _R =3.5V	V _{BR} (V) @ I _T (Note 2)	ŀŢ	V _C (V) @ I _{PP} = 1 A (Note 3)	V _C (V) @MAX I _{PP} (Note 3)	I _{PP} (A) (Note 3)	P_{PK}(W) (Note 3)	C (pF)
Device	Max	Max	Max	Min	mA	Max	Max	Max	Max	Max
FTV05BCSOT883	5.0	0.5	0.3	5.6	1.0	9.8	12.5	5.5	69	15

Other voltage available upon request.

2. V_{BR} is measured with a pulse test current IT at an ambient temperature of 25 $^\circ\!\!\!C$

3. Surge current waveform per Figure 3.

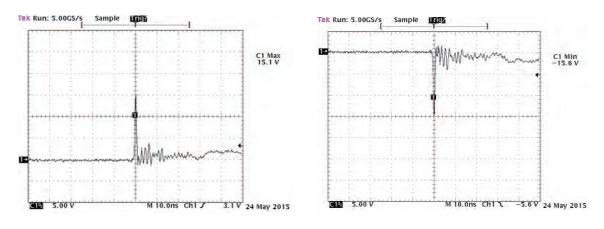
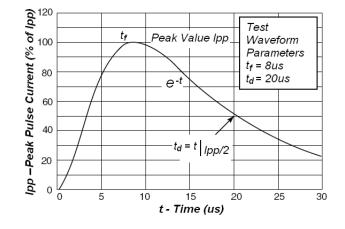


Fig1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2 Fig2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2





FTV05BCSOT883



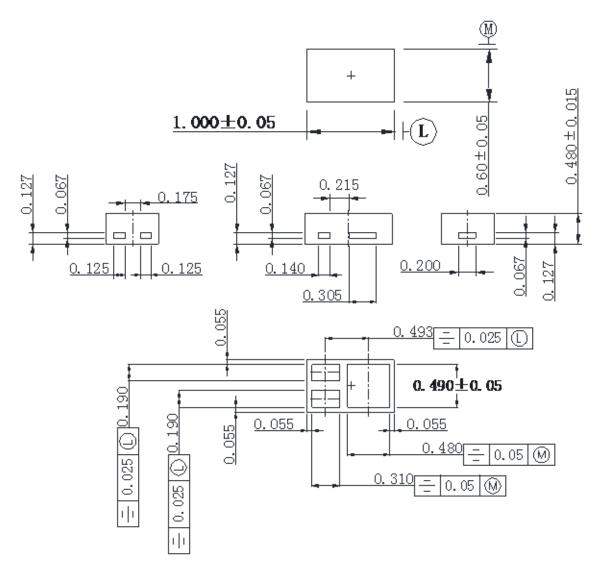




SOT883

Unit:mm

DIMENSION OUTLINE:



First Silicon

4/4